REMARKS

Applicants have carefully reviewed this Application in light of the Office Action mailed January 15, 2003 (Paper No. 6). Claims 1-32 are pending in this Application. Claims 27-32 have been withdrawn due to an election/restriction requirement. Claims 3 and 6 stand rejected under 35 U.S.C. § 112. Claims 1 and 10-12 stand rejected under 35 U.S.C. § 102(e). Claims 2-9, and 13-26 stand rejected under 35 U.S.C. § 103(a). Applicants have amended Claims 3 and 6 to further define various features of Applicants' invention. Applicants respectfully request reconsideration and favorable action in this case.

Restrictions under 35 U.S.C. § 121

During a telephone conference with Examiner Rao, the Examiner required an election between Claims 1-26, drawn to a method of fabricating a conformal film, and Claims 27-32, drawn to a microstructure having a ALO_X. Applicants hereby elect to pursue Claims 1-26. Applicants also hereby cancel Claims 27-32 without prejudice or disclaimer and submit that the cancelled claims are subject to the filing of a divisional application.

Rejection under 35 U.S.C. § 112

Claims 3 and 6 stand rejected by the Examiner under 35 U.S.C. § 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which Applicants regard as the invention.

Applicants have amended Claims 3 and 6 and submit that Claims 3 and 6 now meet the requirements of 35 U.S.C. § 112, second paragraph. Applicants respectfully request that the Examiner reconsider and withdraw the rejections.

Rejection under 35 U.S.C. § 102

Claims 1 and 10-12 stand rejected by the Examiner under 35 U.S.C. § 102(e) as being anticipated by U.S. Patent 6,335,240 issued to Yeong-kwan Kim et al. ("Kim").

Kim discloses a method for forming a capacitor for a semiconductor device that uses a three dimensional storage node with a silicon containing conductive layer to increase capacitance (Col. 2, lines 15-20).

Claim 1 recites, among other elements, a method of fabricating a conformal film on a substrate including the step of "dosing the substrate with a precursor to establish a monolayer of the precursor on the substrate."

Applicants submit that the cited reference fails to disclose each and every element of

Applicants' invention. Kim fails to disclose a method including, "dosing the substrate with a precursor to establish a monolayer of the precursor on the substrate," as recited in Claim 1. The cited reference fails to disclose the recited limitations and, therefore, cannot anticipate Claim 1.

Given that Claims 10-12 depend from Claim 1, Applicants respectfully submit that Claims 10-12 are allowable. As such, Applicants respectfully request that the Examiner withdraw the rejections and allow Claims 1 and 10-12.

Rejection under 35 U.S.C. § 103

Claims 2-9, 13-14 and 16-26 stand rejected under 35 U.S.C. § 103(a) as being unpatentable over Kim as applied to Claim 1 above and further in view of U.S. Patent Publication No. US 2002/0106846 filed by Sean M. Seutter et al. ("Seutter").

Claim 15 stands rejected under 35 U.S.C. § 103(a) as being unpatentable over Kim and Seutter as applied to the claims above and further in view of U.S. Patent No. 5,616,177 issued to Norihide Yamada.

Seutter discloses a method of forming a tantalum-nitride layer film for use in integrated circuit fabrication (Page 1, Paragraph [009]).

Claim 17 recites, among other elements, a method for fabricating a thin AlO_X film on a substrate including the step of "performing plural atomic layer deposition cycles, each cycle comprising deposition of AlO_X by reacting a monolayer of precursor on the substrate with a reactant."

Applicants respectfully submit that the cited references fail to disclose every element of Applicants' invention. Further, there is no motivation, suggestion or teaching to combine Kim and Seutter. For instance, neither Kim nor Seutter teach, disclose or suggest a method for fabricating a thin AlO_X film on a substrate including the step of "performing plural atomic layer deposition cycles, each cycle comprising deposition of AlO_X by reacting a monolayer of precursor on the substrate with a reactant," as recited by Claim 17. The cited references fail to disclose the recited limitations and, therefore, cannot render obvious Claim 17.

Given that Claims 2-9 and 13-16 depend from Claim 1 and Claims 18-26 depend from Claim 17, Applicants respectfully submit that Claims 2-9, 13-16 and 18-26 are allowable. As such, Applicants respectfully request that the Examiner withdraw the rejections and allow Claims 2-9, 13-16 and 17-26.

CONCLUSION

Applicants appreciate the Examiner's careful review of the application. Applicants have now made an earnest effort to place this case in condition for allowance in light of the amendments and remarks set forth above. For the foregoing reasons, Applicants respectfully request reconsideration of the rejections and full allowance of Claims 1-26 as amended.

Applicants enclose a Change of Correspondence Address.

The Commissioner is hereby authorized to charge any fees or credit any overpayments to Deposit Account No. 50-2148 of Baker Botts L.L.P.

If there are any matters concerning this application that may be cleared up in a telephone conversation, please contact Applicants' attorney at 512.322.2581.

Respectfully submitted,

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